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Original Paper

Resonant Raman scattering in InGaAs/AlAs quantum dots

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Abstract

We report resonant Raman scattering from InGaAs/AlAs quantum dots with indium content $x = 0.3 \div 1$. The first order Raman spectra reveal resonant behaviour selective to a quantum dot size. Up to third-order multi-phonon processes have been observed in the quantum dot structure. (© 2006 WILEY-VCH Verlag GmbH & Co. KGaA, Weinheim)

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